	Monday Sept. 14th	Tuesday Sept. 15th	Wednesday Sept. 16th	Thursday Sept. 17th
08:30	10:00 Opening & plenary session	T. Shubina K2 (I5) InN/In nanocomposites: plasmonic effects and optical properties	F. Bechstedt K4 (I13) Spectral properties of InN and related compounds from first principles W1	
09:00				
09:15		A. Vilalta-Clemente(O6) Investigation of InN layers grown by molecular beam epitaxy on Si or GaN templates	I. Gorczyca (I14) In-segregation induced anomalous behavior of band gap and its pressure coefficient in InAlN and InGaN. Theory and Experiment	
		J. Raethel (O7) Optical anisotropy of a- and m-plane InN grown on free-standing GaN substrates		
		E. Sakalauskas (O8) Optical properties of InN grown on Si(111) substrate	C. Van de Walle K5 (I15) Sources of doping for InN bulk and surfaces W2	
10:00		A. Bhattacharya (I6) MOVPE growth and characterization of InN and related heterostructures		
10:30		***Coffee Break (20 min)***		
11:00		Briot (I7) Recent advances in the MOVPE growth of Indium Nitride	A. Yoshikawa K6 (I16) Recent advances and challenges in p-type doping of InN and InN-based novel nanostructures	
		C. Trager-Cowan (O9) Luminescence and structural studies of In-containing III-nitrides		
11:30		Valdueza-Felip (O10) Morphological, structural and optical properties of high-quality InN on GaN-template films deposited by RF sputtering	T. Veal (I17) Interface, bulk and surface electronic properties of InN W3	
12:00		A. Yamamoto K3 (I8) Recent Advances in InN-based Solar Cells; Status and Challenges in InGaN and InAlN Solar Cells	J. Speck (I18) Progress in the MBE Growth of InN	

12:30	***Lunch Break***			
14:00	W. Walukiewicz K1 (I1) Applications of group III-nitride alloys for multijunction solar cells	T. Yamaguchi (I9) Growth of InN and Related Alloys Using Droplet Elimination by Radical Beam Irradiation	H. Morkoc K7 (I19) New Twists in LEDs and HFETs based on Nitride Semiconductors W4	
		N. Kaufmann (O11) Study on Indium Gallium Nitride Quantum Wells: A Comparison between MBE grown and MOVPE grown Quantum Wells		
14:45	J.M. Routoure (O1) Low frequency noise measurements in InN films	C. Rauch (O12) In-vacancies in Si-doped InN	D. Cavalcoli K8 Capacitance and surface voltage charge techniques W5	
15:00	M.A. Poisson (I2) LPMOCVD growth of InAlN/GaN HEMT heterostructures. Comparison of composite SiCopSiC and bulk SiC substrates for HEMT device applications	Inushima (I10) Meissner effect of superconducting InN		
15:30	***Coffee Break (20 min)***			
15:50	C. Wentzel (I3) Wavelength-Stable Green Light Emitting Diodes in Non-Polar GaInN/GaN Quantum Well Growth	C.L Wu (I11) Cross-sectional scanning photoelectron microscopy/spectroscopy studies on the electronic structures of InN surface and interface	R. Butté K9 Optical properties of low-dimensional nitride semiconductors W6	
16:20	P. Komninou (O2) Microstructure of InN grown on Si (111) by plasma-assisted MBE using a double buffer layer	A. Eisenhardt (O12) Changes in the valence band structure of as-grown InN(0001) surfaces upon exposure to oxygen and water		
16:35	Y. Ishitani (O3) Effects of threading dislocations and other defects on reduction of band-edge photoluminescence in n-InN films	B. Hourahine (O13) Vacancies in InN and In rich InGaN	R. Goldhan K10 Optical properties of bulk-like nitride semiconductors W7	
16:50	P. Ruterana (O4) The microstructure and properties of InN layers	X. Wang (O14) Polarity determination of InN by using circular photogalvanic effect		
17:05	M. Zhu (O5) Inclined Dislocation Pair Formation as a Mechanism of Partial Strain Relaxation in GaInN/GaN Quantum Wells on Low-Dislocation Density Bulk GaN	C. Friedrich (O15) Preparation and surface structure of InN(0001) and In_{x}Ga_{1-x}N(0001) surfaces		
17:20	A. Kikuchi (I4) InGaN/GaN nanocolumn LEDs and selective area growth of GaN nano-crystals by rf-plasma assisted molecular beam epitaxy	M.A. Sanchez (I12) MBE growth and characterization of InN-based layers and nanostructures for infrared applications		
17:35				
17:50				
18:05				